

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-IC

TLP115A

HIGH SPEED, LONG DISTANCE ISOLATED LINE RECEIVER

MICROPROCESSOR SYSTEM INTERFACES

DIGITAL ISOLATION FOR A/D, D/A CONVERSION

COMPUTER-PERIPHERAL INTERFACES

GROUND LOOP ELIMINATION

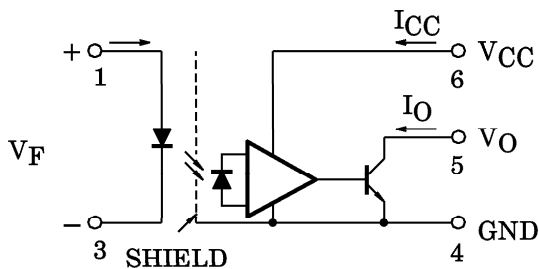
The TOSHIBA MINI FLAT COUPLER TLP115A is a small outline coupler, suitable for surface mount assembly.

TLP115A consists of a high output power GaAs light emitting diode, optically coupled to an integrated high gain, high speed shielded photo detector whose output is an open collector schottky clamped transistor.

The shield, which shunts capacitively coupled common noise to ground, provides a guaranteed transient immunity specification of 1000V / μ s.

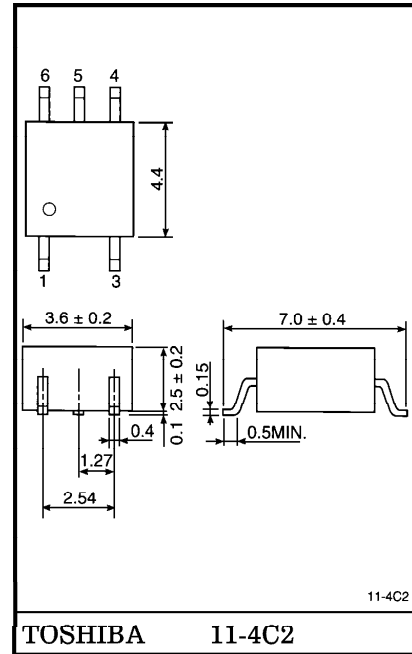
- Input Current Thresholds : $I_F = 5\text{mA (Max.)}$
- Switching Speed : 10MBd (Typ.)
- Common Mode Transient Immunity : $\pm 1000\text{V} / \mu\text{s (Min.)}$
- Guaranteed Performance Over Temp. : 0~70°C
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

SCHEMATIC



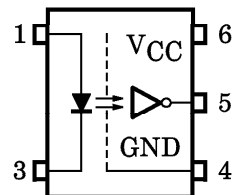
Note. A 0.1 μ F bypass capacitor must be connected between pins 4 and 6.

Unit in mm



Weight : 0.09g

PIN CONFIGURATION (TOP VIEW)



- 1 : ANODE
- 3 : CATHODE
- 4 : GND
- 5 : V_O (OUTPUT)
- 6 : V_{CC}

TRUTH TABLE (Positive Logic)

INPUT	OUTPUT
H	L
L	H

961001EBC2

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● Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

● The products described in this document are subject to foreign exchange and foreign trade control laws.

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● The information contained herein is subject to change without notice.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Note 1)	I _F	20	mA
	Pulse Forward Current (Note 2)	I _{FP}	40	mA
	Peak Transient Forward Current (Note 3)	I _{FPT}	1	A
	Reverse Voltage	V _R	5	V
DETECTOR	Output Current	I _O	25	mA
	Output Voltage	V _O	7	V
	Supply Voltage (1 Minute Maximum)	V _{CC}	7	V
	Output Power Dissipation	P _o	40	mW
Operating Temperature Range		T _{opr}	-40~85	°C
Storage Temperature Range		T _{stg}	-55~125	°C
Lead Solder Temperature (10 sec.)		T _{sol}	260	°C
Isolation Voltage (AC, 1 min., RH ≤ 60%, Note 4)		BVS	2500	V _{rms}

(Note 1) Derate 0.36mA/°C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width. Derate 0.72mA/°C above 70°C.

(Note 3) Pulse width ≤ 1μs, 300pps.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input Voltage, Low Level	V _{FL}	-3	0	1.0	V
Input Current, High Level	I _{FH}	6.3	8	20	mA
Supply Voltage	V _{CC}	4.5	5	5.5	V
Fan Out (TTL Load, Each Channel)	N	—	—	8	—
Operating Temperature	T _{opr}	0	—	70	°C

ELECTRICAL CHARACTERISTICS (Unless otherwise specified, $T_a = 0 \sim 70^\circ\text{C}$, $V_{CC} = 4.5 \sim 5.5\text{V}$, $V_{FL} \leq 1.0\text{V}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F = 10\text{mA}$, $T_a = 25^\circ\text{C}$	1.2	1.4	1.7	V
Forward Voltage Temperature Coefficient	V_F / T_a	$I_F = 10\text{mA}$	—	-2	—	mV / °C
Reverse Current	I_R	$V_R = 3\text{V}$, $T_a = 25^\circ\text{C}$	—	—	10	μA
Capacitance Between Terminals	C_T	$V_F = 0$, $f = 1\text{MHz}$, $T_a = 25^\circ\text{C}$	—	30	—	pF
High Level Output Voltage	I_{OH}	$V_F = 1.0$, $V_O = 5.5\text{V}$	—	—	250	μA
		$V_F = 1.0$, $V_O = 5.5\text{V}$, $T_a = 25^\circ\text{C}$	—	0.5	10	
Low Level Output Current	V_{OL}	$I_F = 5\text{mA}$ $I_{OL} = 13\text{mA}$ (Sinking)	—	0.4	0.6	V
“H Level Output → L Level Output” Input Current	I_{FH}	$I_{OL} = 13\text{mA}$ (Sinking) $V_{OL} = 0.6\text{V}$	—	—	5	mA
High Level Supply Current	I_{CCH}	$V_{CC} = 5.5\text{V}$, $I_F = 0$	—	7	15	mA
Low Level Supply Current	I_{CCL}	$V_{CC} = 5.5\text{V}$, $I_F = 10\text{mA}$	—	12	19	mA
Input-Output Insulation Leakage Current	I_S	$V_S = 3540\text{V}$, $t = 5\text{s}$ $T_a = 25^\circ\text{C}$ (Note 4)	—	—	100	μA
Isolation Resistance	R_S	R.H. $\leq 60\%$, $V_S = 500\text{V DC}$ $T_a = 25^\circ\text{C}$ (Note 4)	5×10^{10}	10^{14}	—	Ω
Stray Capacitance Between Input to Output	C_S	$V_S = 0$, $f = 1\text{MHz}$ $T_a = 25^\circ\text{C}$ (Note 4)	—	0.8	—	pF

* All typical values are $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$.

SWITCHING CHARACTERISTICS ($V_{CC} = 5V$, $T_a = 25^\circ C$)

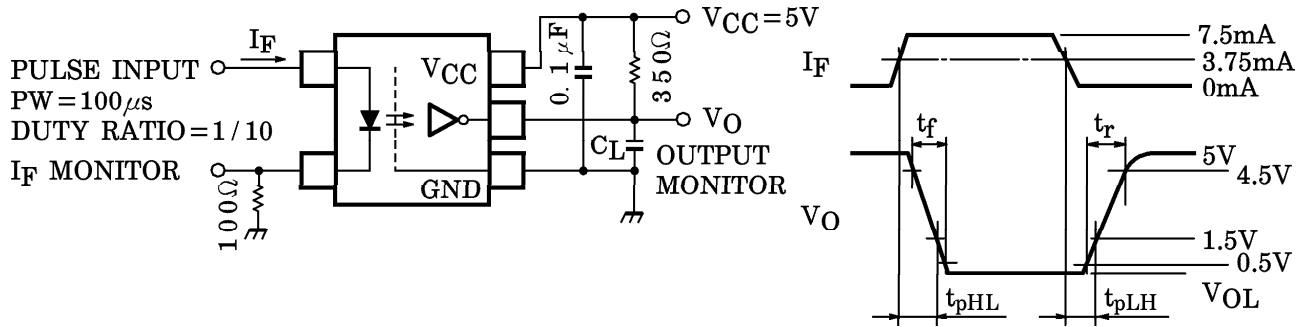
CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time (H→L)	t_{pHL}	1	$I_F = 0 \rightarrow 7.5mA$ $C_L = 15pF$, $R_L = 350\Omega$	—	60	120	ns
Propagation Delay Time (L→H)	t_{pLH}	1	$I_F = 7.5 \rightarrow 0mA$ $C_L = 15pF$, $R_L = 350\Omega$	—	60	120	ns
Output Rise Fall Time (10-90%)	t_r , t_f	2	$R_L = 350$, $C_L = 15pF$ $I_F = 0 \rightleftharpoons 7.5mA$	—	30	—	ns
Common Mode Transient Immunity at High Output Level	CM_H	2	$I_F = 0mA$, $V_{CM} = 400V_{p-p}$ $V_{O(MIN)} = 2V$, $R_L = 350\Omega$	1000	—	—	V / μs
Common Mode Transient Immunity at Low Output Level	CM_L	2	$I_F = 7.5mA$, $V_{CM} = 400V_{p-p}$ $V_{O(MAX)} = 0.8V$, $R_L = 350\Omega$	-1000	—	—	V / μs

(Note 4) Device considered a two-terminal device : Pins 1 and 3 shorted together, and pins 4, 5 and 6 shorted together.

(Note 5) The V_{CC} supply voltage to each TLP115A isolator must be bypassed by $0.1\mu F$ capacitor. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to package V_{CC} and GND pins of each device.

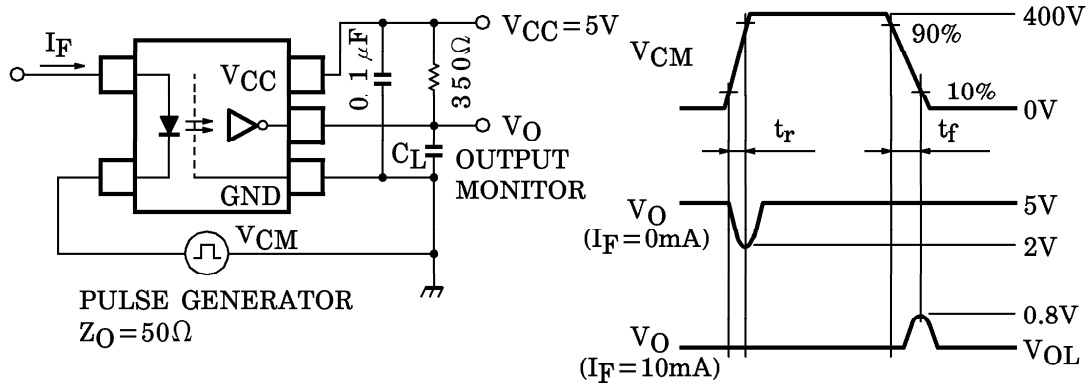
(Note 6) Maximum electrostatic discharge voltage for any pins : 180V ($C = 200pF$, $R = 0$)

TEST CIRCUIT 1 : Switching Time Test Circuit



C_L is approximately 15pF which includes probe and stray wiring capacitance.

TEST CIRCUIT 2 : Common Mode Transient Immunity Test Circuit



$$CM_H = \frac{320(V)}{t_r(\mu s)}, \quad CM_L = \frac{320(V)}{t_f(\mu s)}$$

C_L is approximately 15pF which includes probe and stray wiring capacitance.

